

# A facile route for the preparation of nanoparticles of the spin-crossover complex $[\text{Fe}(\text{Htrz})_2(\text{trz})](\text{BF}_4)$ in xerogel transparent composite films

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## Electronic Supplementary Information

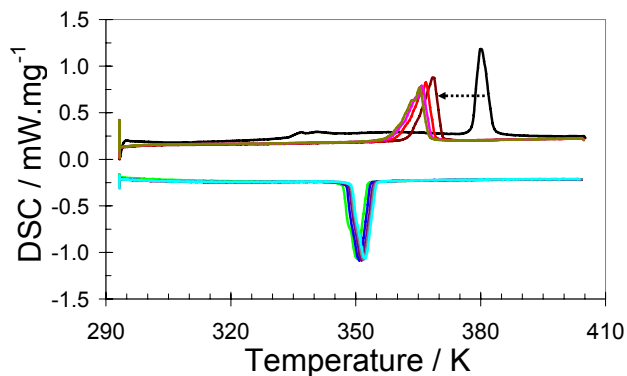


Fig. S1. DSC measurements of the bulk starting  $[\text{Fe}(\text{Htrz})_2(\text{trz})](\text{BF}_4)$  **1b**. Arrow shows the shift of the position of the peak after repetitive heating-cooling cycles of temperature

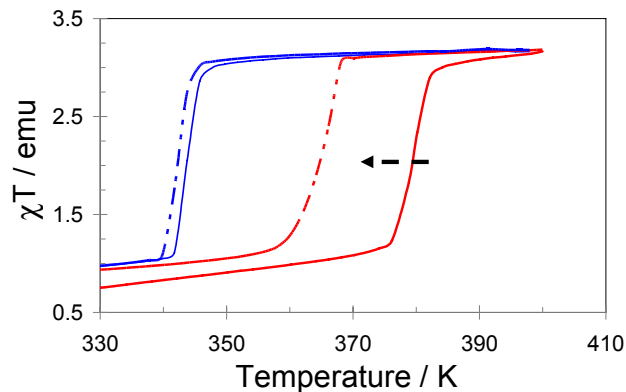


Fig. S3.  $\chi T$  as a function of the temperature for the bulk starting  $[\text{Fe}(\text{Htrz})_2(\text{trz})](\text{BF}_4)$  **1b**. Arrow shows the decrease of the hysteresis loops width after one heating-cooling cycle of temperature

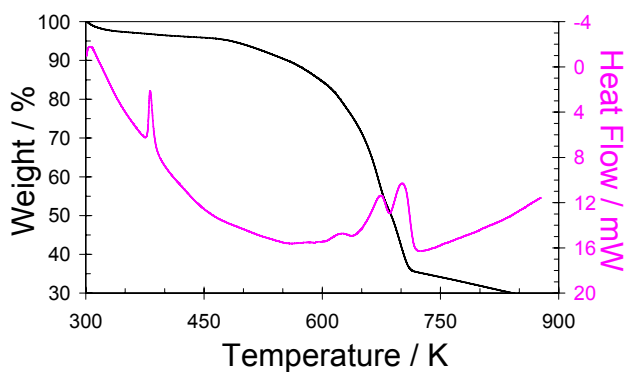


Fig. S2. TGA-TDA measurements for the bulk starting  $[\text{Fe}(\text{Htrz})_2(\text{trz})](\text{BF}_4)$  **1b**

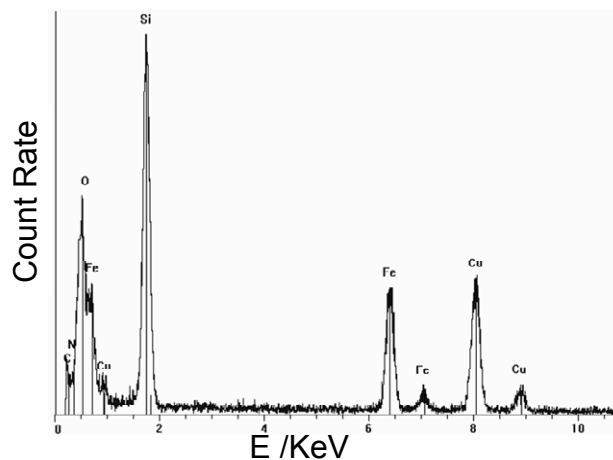


Fig. S4. EDX of an assembly of particles of **1b**@SiO<sub>2</sub> (in TMOS) observed by high resolution microscopy.

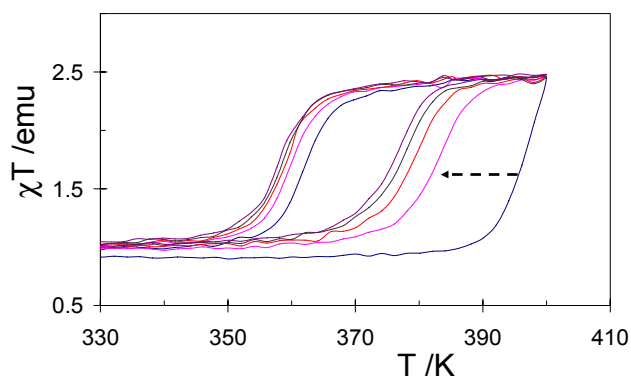


Fig. S5.  $\chi T$  as a function of the temperature for the films of **1b**@SiO<sub>2</sub> (in TMOS). Arrow shows the decrease of the hysteresis loops width after repetitive heating-cooling cycles of temperature

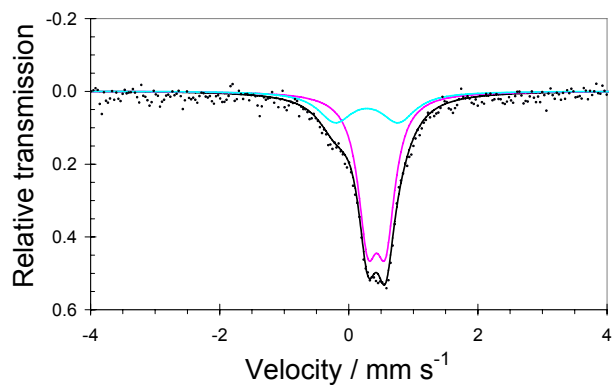


Fig. S8. Mössbauer spectra of **1b**@SiO<sub>2</sub> (in TMOS) at 293 K

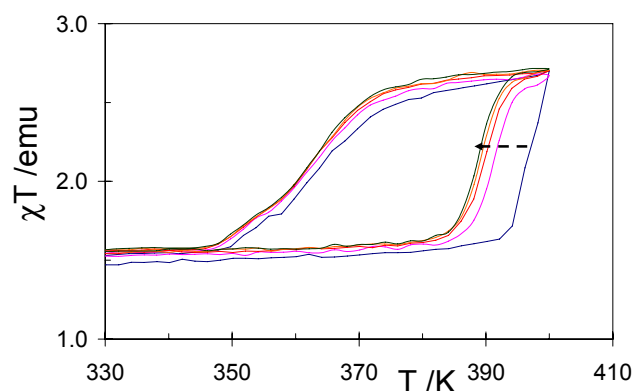


Fig. S6.  $\chi T$  as a function of the temperature for the monoliths of **1b**@SiO<sub>2</sub> (in TMOS). Arrow shows the decrease of the hysteresis loop width after repetitive one heating-cooling cycle of temperature

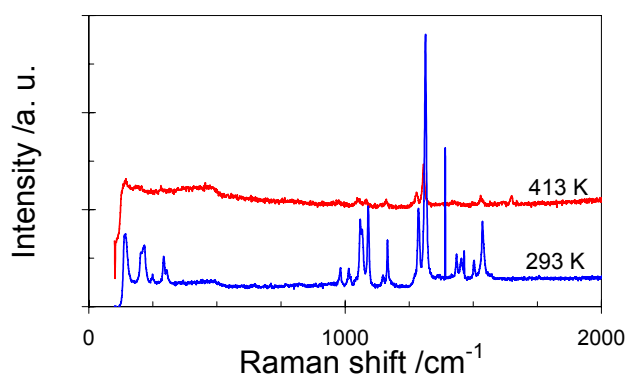


Fig. S9. Raman spectrum of films of **1b**@SiO<sub>2</sub> in TEOS at 293 and 413 K between 100 and 2000 cm<sup>-1</sup>

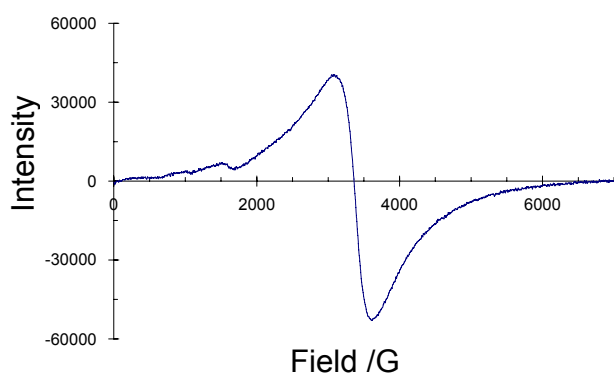


Fig. S7. EPR spectrum of **1b**@SiO<sub>2</sub> (in TMOS) at 293 K.

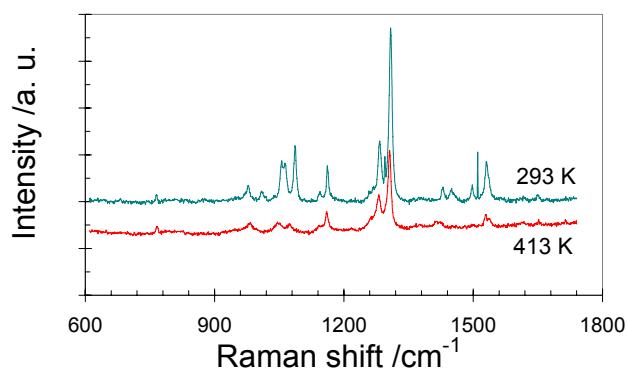


Fig. S10. Raman spectrum of films of **1b**@SiO<sub>2</sub> in TMOS at 293 and 413 K between 600 and 1700 cm<sup>-1</sup>

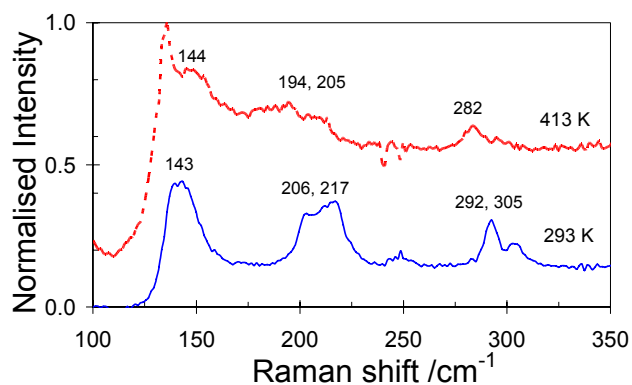


Fig. S11. Raman spectrum of films of **1b**@SiO<sub>2</sub> in TEOS at 293 and 413 K between 100 and 350 cm<sup>-1</sup>

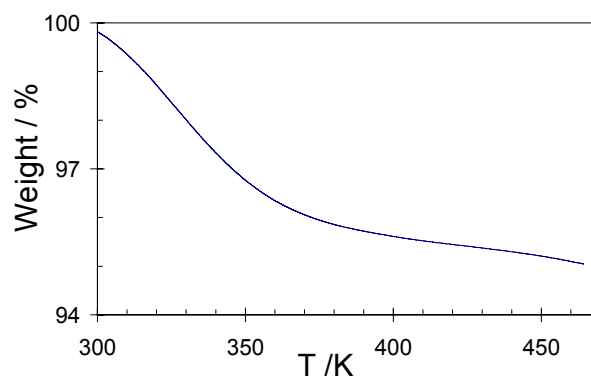
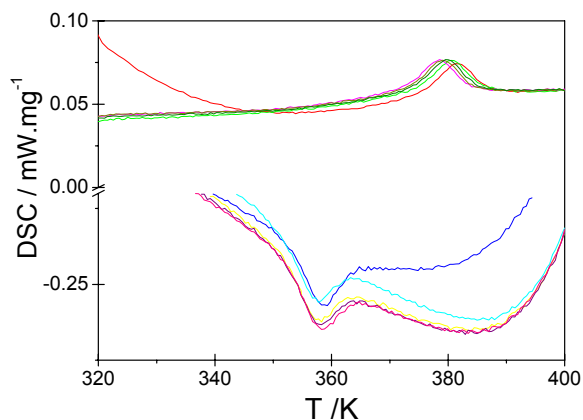


Fig. S14. TGA of film of **1b**@SiO<sub>2</sub> in TMOS



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Fig. S12. DSC measurements of films of **1b**@SiO<sub>2</sub> in TMOS with repetitive heating-cooling cycles of temperature

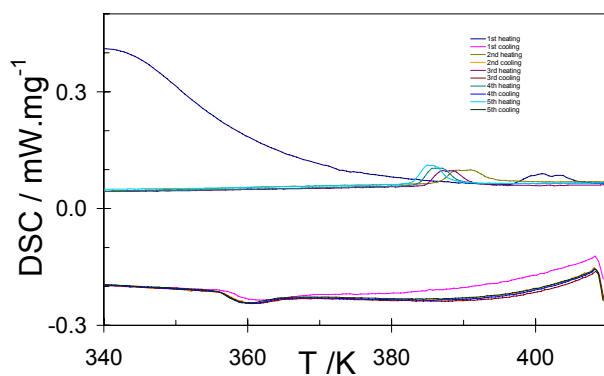


Fig. S13. DSC measurements of films of **1b**@SiO<sub>2</sub> in TEOS with repetitive heating-cooling cycles of temperature

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